

TOSHIBA FIELD EFFECT TRANSISTOR GaAs N-CHANNEL DUAL GATE MES TYPE

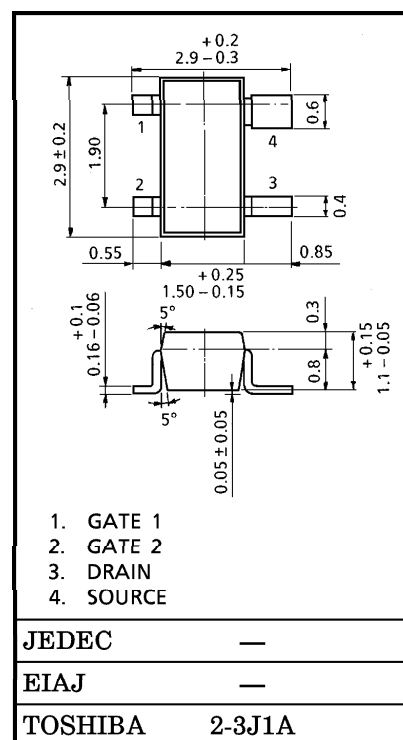
3SK240

TV TUNER, UHF RF AMPLIFIER APPLICATIONS

Unit in mm

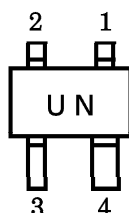
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate1-Drain Voltage	V _{G1D0}	−9	V
Gate2-Drain Voltage	V _{G2D0}	−9	V
Gate1-Source Voltage	V _{G1S}	−4	V
Gate2-Source Voltage	V _{G2S}	−4	V
Gate1 Current	I _{G1}	1	mA
Gate2 Current	I _{G2}	1	mA
Power Dissipation	P _D	150	mW
Channel Temperature	T _{ch}	125	°C
Storage Temperature Range	T _{stg}	−55~125	°C



Weight : 0.013g

MARKING



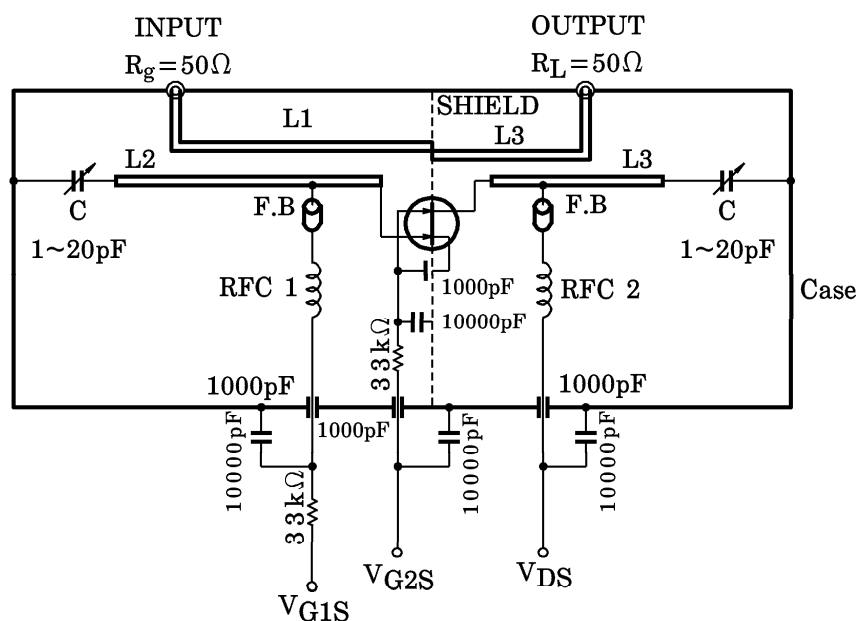
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate1 Leakage Current	I _{G1SS}	V _{DS} =0, V _{G1S} =−3V, V _{G2S} =0	—	—	−4	μA
Gate2 Leakage Current	I _{G2SS}	V _{DS} =0, V _{G1S} =0, V _{G2S} =−3V	—	—	−4	μA
Drain Current	I _{DSS}	V _{DS} =3V, V _{G1S} =0, V _{G2S} =0	6	—	20	mA
Gate1-Source Cut-off Voltage	V _{G1S} (OFF)	V _{DS} =3V, V _{G2S} =0, I _D =100μA	−0.7	—	−1.8	V
Gate2-Source Cut-off Voltage	V _{G2S} (OFF)	V _{DS} =3V, V _{G1S} =0, I _D =100μA	−0.7	—	−1.8	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =3V, V _{G2S} =1V, I _D =5mA f=1kHz	—	19	—	ms
Input Capacitance	C _{iss}	V _{DS} =3V, V _{G2S} =1V, I _D =5mA f=1kHz	—	0.6	1.4	pF
Reverse Transfer Capacitance	C _{rss}		—	0.013	0.030	pF
Power Gain	G _{ps}	V _{DS} =3V, V _{G2S} =1V, I _D =5mA f=800MHz (Fig.1)	17	20.5	—	dB
Noise Figure	NF		—	1.0	2.0	dB

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Fig.1 800MHz Gps, NF TEST CIRCUIT



L1~L4 : ϕ 1.0mm SILVER PLATED COPPER WIRE

C : AIR TRIMMER TTA25A200A (MURATA MFG. Co., LTD.)

RFC 1 : ϕ 0.35mm COPPER WIRE 3mm ID, 7T

RFC 2 : ϕ 0.35mm COPPER WIRE 3mm ID, 10T

CAUTION

GaAs (Gallium Arsenide) is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this product properly according to law. Do not intermingle with normal industrial or domestic waste.

